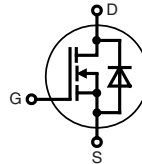


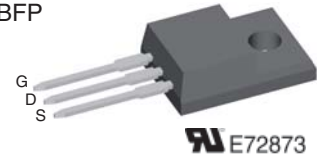
CoolMOS™ 1) Power MOSFET

Fully isolated package
 N-Channel Enhancement Mode
 Low $R_{DS(on)}$, High V_{DSS} MOSFET
 Ultra low gate charge

Preliminary data



TO-220 ABFP



$$I_{D25} = 5.4 \text{ A}$$

$$V_{DSS} = 600 \text{ V}$$

$$R_{DS(on) \text{ max}} = 0.385 \Omega$$

MOSFET			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	5.4	A
I_{D90}	$T_C = 90^\circ\text{C}$	3.7	A
E_{AS}	single pulse } $I_D = 3.4 \text{ A}; T_C = 25^\circ\text{C}$ repetitive	225	mJ
E_{AR}		0.3	mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50	V/ns

Features

- Fast CoolMOS™ 1) power MOSFET 4th generation
- High blocking capability
- Lowest resistance
- Avalanche rated for unclamped inductive switching (UIS)
- Fully isolated package

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 5.2 \text{ A}$		350	385	m Ω
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 0.34 \text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}$			1	μA
				10	μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100	nA
C_{iss}	} $V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$		790		pF
C_{oss}				38	
Q_g	} $V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 5.2 \text{ A}$		17	22	nC
Q_{gs}			4		nC
Q_{gd}			6		nC
$t_{d(on)}$	} $V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 5.2 \text{ A}; R_G = 3.3 \Omega$		10		ns
t_r			5		ns
$t_{d(off)}$			40		ns
t_f			5		ns
R_{thJC}				3.95	K/W

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

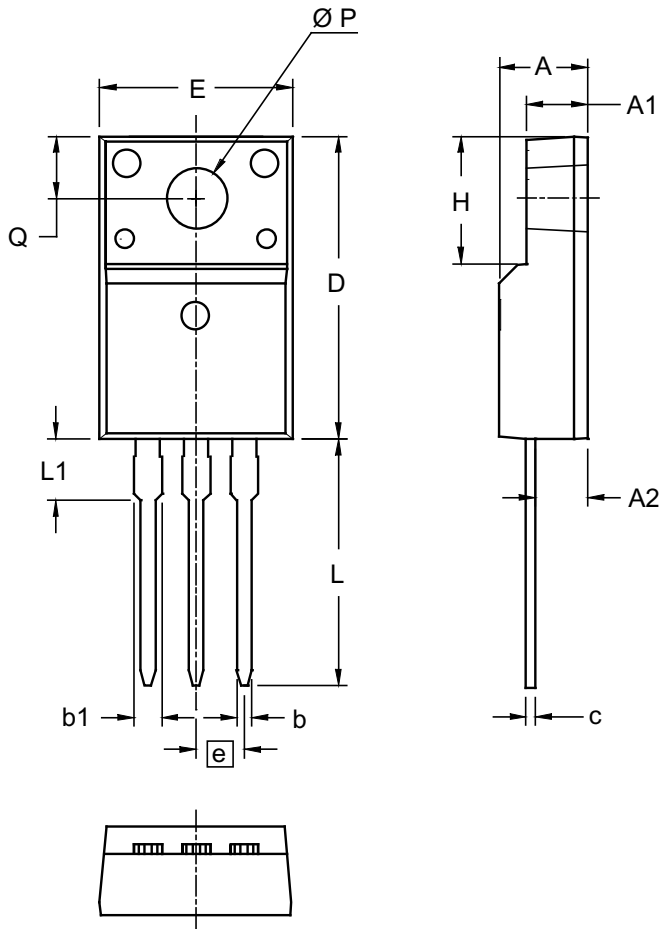
Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)					
I_S	$V_{GS} = 0\text{ V}$			5.2	A
V_{SD}	$I_F = 5.2\text{ A}; V_{GS} = 0\text{ V}$		0.9	1.2	V
t_{rr}	} $I_F = 5.2\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 400\text{ V}$		260		ns
Q_{RM}			21		μC
I_{RM}			24		A

Component

Symbol	Conditions	Maximum Ratings			
		min.	typ.	max.	
T_{VJ}	operating		-55...+150		$^{\circ}\text{C}$
T_{stg}			-55...+150		$^{\circ}\text{C}$
M_d	mounting torque		0.4 ... 0.6		Nm
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
R_{thCH}	with heatsink compound		0.50		K/W
R_{thJA}	thermal resistance junction - ambient		80		K/W
Weight			2		g

TO-220 ABFP Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

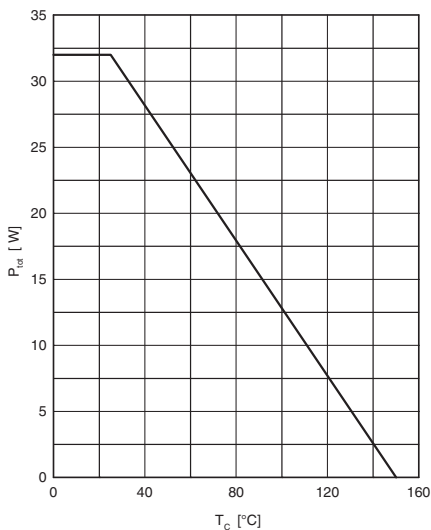


Fig. 1 Power dissipation

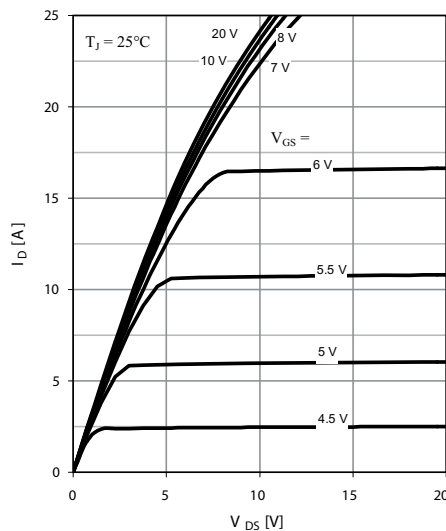


Fig. 2 Typ. output characteristics

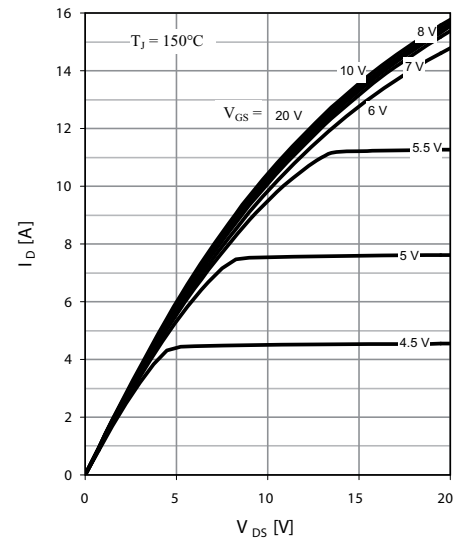


Fig. 3 Typ. output characteristics

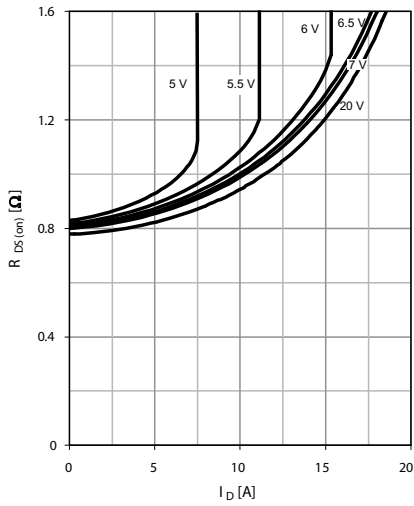


Fig. 3 Typ. drain-source on-state resistance characteristics of IGBT

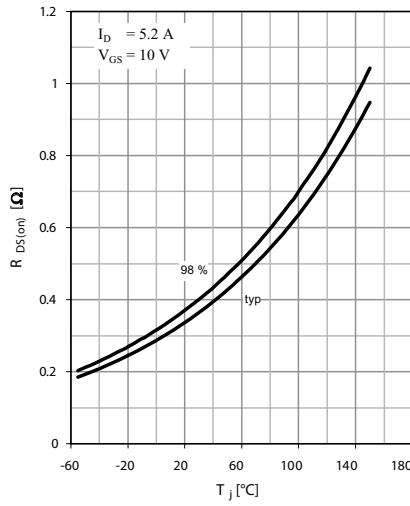


Fig. 4 Drain-source on-state resistance

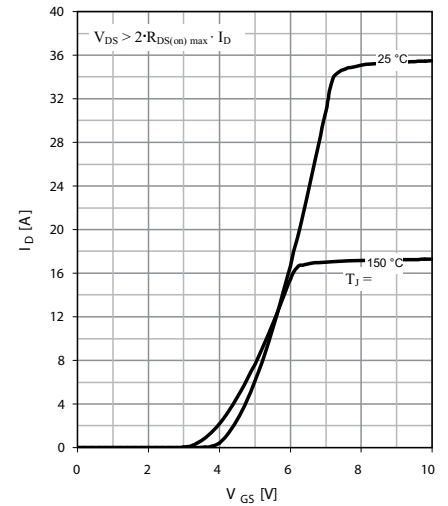


Fig. 5 Typ. transfer characteristics

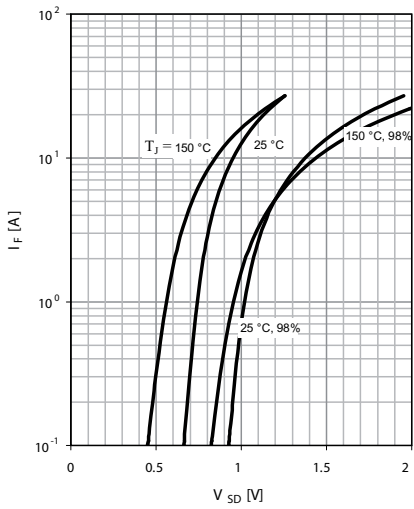


Fig. 6 Forward characteristic of reverse diode

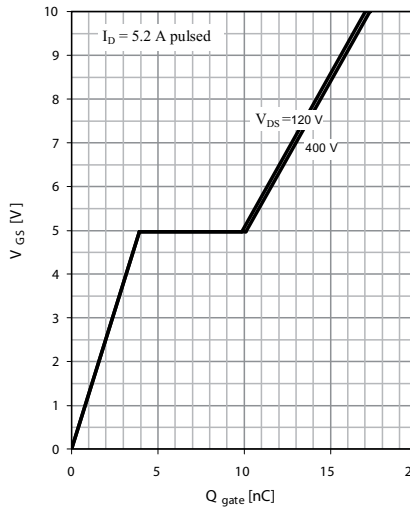


Fig. 7 Typ. gate charge

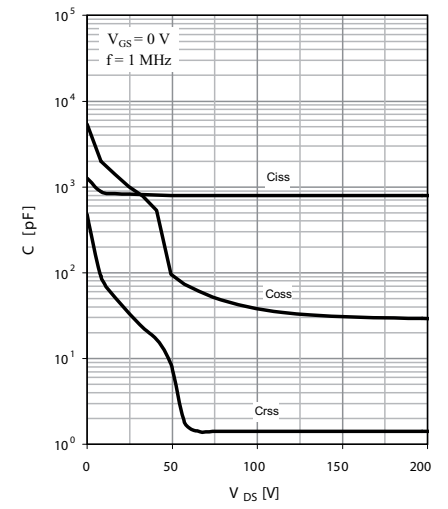


Fig. 8 Typ. capacitances

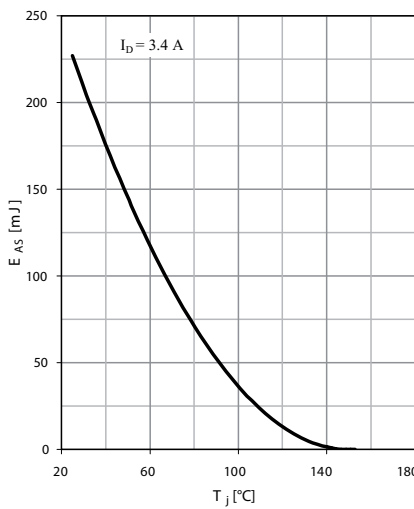


Fig. 9 Avalanche energy

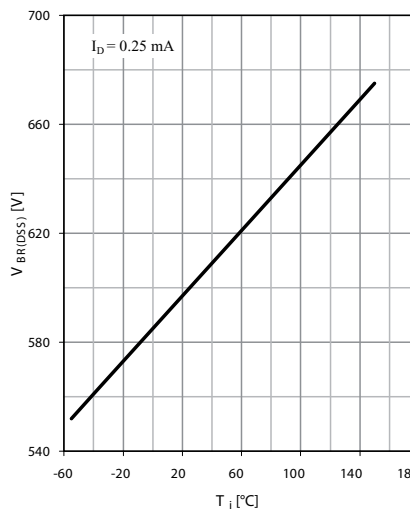


Fig. 10 Drain-source breakdown voltage